

<b>INFORMATION DISCLOSURE STATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional) <b>F03-354-USDiv</b>		Application Number <b>10/634,836</b>	
				Applicant(s) <b>Hisaki KATO, et al.</b>			
				Filing Date <b>August 6, 2003</b>		Group Art Unit <b>2822</b>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>FOREIGN PATENT DOCUMENTS</b>							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES      NO
		<b>H7-7182</b>	<b>01/10/99</b>	<b>Japan</b>			<i>abs</i>
				<i>not considered</i>			
				<i>not considered</i>			
				<i>not considered</i>			
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
		Japanese Office Action, dated May 24, 2005, with partial English translation					
		<i>not considered</i>					
		NAKAMURA, et al., "Ridge-geometry InGaN multi-quantum-well-structure laser diodes", APPLIED PHYSICS LETTERS, September 2, 1996, Vol. 69, No. 10, pp. 1477-1479					
<i>not considered</i>							
EXAMINER				DATE CONSIDERED			
<b>EXAMINER:</b> Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							